

OFFICE OF NAVAL RESEARCH

FINAL TECHNICAL REPORT

for

Contract N00014-86-K-0545

R&T Code 4134011

"Studies of Chemistry and Diffusion on Silicon and Gallium Arsenide Surfaces Using Laser-Induced Thermal Desorption"

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### I. Overview

### A. Principal Investigator

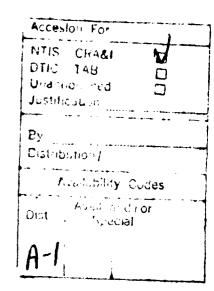
Dr. Steven M. George Dept. of Chemistry Stanford University Stanford, Calif. 94305

### B. Cognizant ONR Scientific Officer

Dr. David L. Nelson / Dr. Mark Ross

### C. Current Telephone Numbers

(415) 725-0270 (Office) (415) 723-5918 (Lab) (415) 723-1236 (Secretary)



### D. Brief Description of Completed Project

Surface chemistry and surface diffusion play pivotal roles in semiconductor processing and must be understood as electronic device dimensions approach the submicron level. In this project, basic time-dependent processes on silicon surfaces were examined using laser induced thermal desorption (LITD) and Fourier transform infrared (FTIR) spectroscopy. These techniques provided direct, quantitative measurements of surface coverage in real-time. Using LITD and FTIR techniques, emphasis was on a microscopic understanding of semiconductor surface reaction kinetics.

The major areas addressed were the kinetics of fundamental semiconductor processing steps such as: surface oxidation and nitridation; epitaxial growth on surfaces; and surface etching. The Si(111)7x7 single crystal surface, as well as porous silicon surface, were used as the model semiconductor surfaces. These studies were conducted in UHV using Auger spectroscopy and LEED spectroscopy for surface analysis and characterization. The kinetic parameters that were determined by these LITD and FTIR studies are crucial for the understanding and modeling of semiconductor processing chemistry.

### II. Significant Results from ONR Contract Support

This ONR sponsored research addressed the kinetics of fundamental surface reactions relevant to semiconductor processing chemistry. This section will highlight the research that has been published recently in refereed journals. Our more recent research on various chlorosilanes and chlorogermanes that are important in silicon and germanium epitaxy was initiated at the end of this ONR contract support and is still under investigation. This research will be discussed in future end-of-the-year reports for ONR N00014-90-J-1281.

### A. Hydrogen Desorption Kinetics from Silicon Surfaces

Hydrogen plays a key role in silicon surface chemistry. Our initial LITD and FTIR studies explored the desorption kinetics of  $\rm H_2$  from Si(111)7x7 and porous silicon surfaces [1-3]. These investigations established the different thermal stabilities of monohydride and dihydride species. Moreover, these studies obtained kinetic parameters for monohydride and dihydride desorption. These kinetic parameters are useful for understanding the basic interaction of hydrogen with silicon surfaces and for modeling various CVD silicon processing steps.

# B. Adsorption Kinetics of O<sub>2</sub> on Si(111)7x7

Oxygen forms an insulating oxide layer upon reaction with silicon surfaces. The details of oxygen adsorption and oxide growth in the submonolayer and monolayer regime have been debated actively. Our second major study addressed the initial growth of the silicon oxide layer on Si(111)7x7 [6,8]. We measured a

temperature-dependent sticking coefficient that decreased with temperature indicating a precursor adsorption mechanism. In addition, a temperature-dependent apparent saturation coverage was revealed that increased dramatically with surface temperature. These results should be useful for a complete understanding of silicon surface oxidation and models of silicon oxide growth in the thin film limit.

# C. <u>Laser-Induced Desorption of Silicon-Containing Surface</u> Reaction Intermediates

During the examination of the LITD yield from Si(111)7x7 surfaces exposed to H<sub>2</sub>O and NH<sub>3</sub>, we discovered the presence of silicon-containing LITD species in the form of SiOH and SiNH<sub>2</sub> [4]. Additional examination of a hydrogen-saturated Si(111)7x7 surface revealed SiH<sub>2</sub> LITD products. Likewise, the Si(111)7x7 exposed to CH<sub>3</sub>OH produced SiOCH<sub>3</sub> LITD species. These silicon-containing species were intriguing and suggested that laser desorption was able to desorb these surface reaction intermediates directly from the silicon surface. Subsequent FTIR investigations have confirmed that the silicon-containing LITD products correspond to silicon surface reaction intermediates. The ability of LITD to remove these reaction intermediates is extremely useful for kinetic studies of decomposition on silicon surfaces as discussed below.

### D. Decomposition of $H_2O$ on Si(111)7x7

Making use of the ability of LITD to desorb siliconcontaining surface reaction intermediates, the decomposition of  $\rm H_2O$  was examined on Si(111)7x7 [5]. This study established the thermal stability of the SiOH species and monitored its decomposition between 400-600 K prior to  $\rm H_2$  desorption at 800 K and SiO desorption at 950 K. The decomposition kinetics for SiOH were self-poisoning at high coverages suggesting that the availability of free dangling-bond surface sites controls the reaction. Experiments with preadsorbed hydrogen also revealed surface passivation as hydrogen ties up free surface dangling bonds. These results are probably transferable to many decomposition reactions on silicon surfaces and should be especially useful in understanding the formation of insulating silicon oxide layers with  $\rm H_2O$  oxidation.

# E. Decomposition of $NH_3$ on Si(111)7x7

 ${
m NH}_3$  is commonly employed to grow insulating silicon nitride layers. Like  ${
m H}_2{
m O}$  decomposition,  ${
m NH}_3$  decomposes to yield hydrogen on the silicon surface. The availability of free surface sites may also be expected to control the surface reaction rates. By monitoring the  ${
m SiNH}_2$  LITD species, the thermal stability and decomposition rates of the  ${
m SiNH}_2$  surface reaction intermediate were studied on  ${
m Si}(111)7x7$  [7]. The expected parallels between  ${
m SiNH}_2$  and  ${
m SiOH}$  were established. In addition, a  ${
m SiNH}$  LITD species was observed that displayed different decomposition kinetics than  ${
m SiNH}_2$  and suggested a partially step-wise decomposition of  ${
m SiNH}_2$ . Moreover, the effect of preadsorbed hydrogen was observed to passivate the  ${
m Si}(111)7x7$  surface and reduce the  ${
m NH}_3$  decomposition yield. These results should be useful for an understanding of silicon nitride film growth.

### III. Graduate Students Working on Project

Five graduate students worked on various aspects of this ONR sponsored research:

- 1. Chi Mak. Entered Stanford 1984. Graduated 1988. NSF Fellow. Worked on LITD studies of  $H_2$  desorption,  $O_2$  adsorption and  $H_2O$  decomposition on Si(111)7x7. Postdoc work at U.C. Berkeley. Starts faculty position at USC, Fall, 1990.
- 2. Birgit Koehler. Entered Stanford 1985. Graduates Spring 1990. NSF Graduate Fellow. Worked on LITD studies of  $\rm H_2$  desorption,  $\rm H_2O$  and  $\rm NH_3$  decomposition, SiCl<sub>4</sub> adsorption and desorption on Si(111)7x7. Starts postdoc at SRI, summer 1990.
- 3. Kim Gupta. Entered Stanford 1985. Graduates Fall 1990. Worked on FTIR studies of  $\rm H_2$  desorption and  $\rm O_2$  oxidation of porous silicon. Worked on LITD studies of  $\rm O_2$  adsorption, SiCl<sub>4</sub> adsorption and desorption on Si(111)7x7. Accepted job with Intel-Santa Clara, Fall 1990.
- 4. Peter Coon. Entered Stanford 1987. Has worked on all LITD studies of adsorption, decomposition and desorption from Si(111)7x7. Third year student.
- 5. Anne Dillon. Entered Stanford 1988. Has worked on all new FTIR research on  $\rm H_2O$  decomposition and  $\rm NH_3$  decomposition on porous silicon. Second year student.

#### IV. Publications Resulting from ONR Contract

1. Authors: P.Gupta, V.L. Colvin and S.M. George

Title: "Hydrogen Desorption Kinetics from Monohydride

and Dihydride Species on Silicon Surfaces"

Journal: Physical Review B 37, 8234 (1988).

2. Authors: B.G. Koehler, C.H. Mak, D.A. Arthur and S.M.

George

Title: "Desorption Kinetics of Hydrogen from

Si(111)7x7 Studied Using Laser Induced Thermal

Desorption"

Journal: Journal of Chemical Physics 89, 1079, (1988).

3. Authors: P. Gupta, V.L. Colvin, J.L. Brand and S.M.

George

Title: "Hydrogen Desorption Kinetics from Silicon

Surfaces Using Transmission FTIR" in Decomposition and Growth: Limits for

Microelectronics

Publisher: American Vacuum Society, edited by G.W.

Rubloff

4. Authors: C.H. Mak, B.G. Koehler and S.M. George

Title: "Laser-Induced Thermal Desorption of Silicon-

Containing Surface Reaction Intermediates from

Si (111) 7x7"

Journal: Surface Science 208, L42 (1989)

5. Authors: B.G. Koehler, C.H. Mak and S.M. George

"Decomposition of  $H_2O$  on Si(111)7x7 Studied

Using Laser-Induced Thermal Desorption"

Journal: Surface Science 221, 565 (1989)

6. Authors: P. Gupta, C.H. Mak, P.A. Coon and S.M. George

Title: "Oxidation Kinetics of Si(111)7x7 in the

Submonolayer Regime"

Journal: Physical Review B40, 7739 (1989)

7. Authors: B.G. Koehler, P.A. Coon and S.M. George

Title: "Decomposition of NH<sub>3</sub> on Si(111)7x7 Studied Using Laser Induced Thermal Desorption"

Journal: Journal of Vacuum Science Technology <u>B7</u>, 1303 (1989)

8. Authors: S.M. George, P. Gupta, C.H. Mak and P.A. Coon

Title: "Oxidation Kinetics of Silicon Surfaces:
Reactive Sticking Coefficient, Apparent
Saturation Coverage and Effect of Surface
Hydrogen", in Chemical Prospectives of
Microelectronic Materials"

Journal: Material Research Society Symposium Proceedings 131, 169 (1989)

9. Authors: P. Gupta, P.A. Coon, B.G. Koehler and S.M. George

Title: "Adsorption of Silicon Tetrachloride on Si(111)7x7", in Chemical Prospectives of Microelectronic Materials"

Publisher: Material Research Society Symposium Proceedings 131, 197 (1989)

# V. Manuscripts in Press or Preparation Resulting from ONR Contract

1. Authors: P. Gupta, C.H. Mak, P.A. Coon and S.M. George

Title: "Kinetics of H<sub>2</sub>O Adsorption on Si(111)7x7"

Journal: Surface Science Letters (in preparation for

submission

2. Authors: P. Gupta, A.S. Bracker, V.L. Colvin and S.M.

George

Title: "Oxidation Kinetics of Porous Silicon Studied

Using Transmission FTIR"

Journal: Journal of Electrochemical Society (in

preparation for submission)

3. Authors: P. Gupta, P.A. Coon, B.G. Koehler and S.M.

George

Title: "Adsorption and Desorption Kinetics for SiCl4

on Si(111)7x7"

Journal: Journal of Chemical Physics (in press)

4. Authors: P. Gupta, P.A. Coon, B.G. Koehler and S.M.

George

Title: "Adsorption and Desorption Kinetics for Cl2 on

Si (111) 7x7"

Journal: (in preparation for submission)

5. Authors: P. Gupta, P.A. Coon, B.G. Koehler and S.M.

George

Title: "Adsorption and Desorption Kinetics for SiCl<sub>2</sub>H<sub>2</sub>

on Si(111)7x7"

Journal: (in preparation for submission)

6. Authors: P.A. Coon, P. Gupta, B.G. Koehler and S.M.

George

Title: "Surface Hydride Species on Si(111)7x7 Studied

Using Laser Induced Thermal Desorption"

Journal: (in preparation for submission)

7. Authors: B.G. Koehler and S.M. George

Title: "Laser Induced Thermal Desorption from Si(111)7x7: I. Numerical Calculations"

Journal: (in preparation for submission)

8. Authors: P. Gupta, P.A. Coon, B.G. Koehler and S.M. George

Title: "Laser Induced Thermal Desorption from Si(111)7x7: II. Hydrogen Isothermal Desorption Kinetics"

Journal: (in preparation for submission)

9. Authors: P. Gupta, A.C. Dillon, A.S. Bracker and S.M. George

Title: "Decomposition of H<sub>2</sub>O on Silicon Surfaces Studied Using Transmission FTIR"

Journal: (in preparation for submission)

10. Authors: A.C. Dillon, P. Gupta, A.S. Bracker and S.M. George

Title: "Decomposition of NH<sub>3</sub> on Silicon Surfaces Studied Using Transmission FTIR"

Journal: (in preparation for submission)

11. Authors: S.M. George, P. Gupta, B.G. Koehler, C.H. Mak and P.A. Coon

Title: "Laser Induced Thermal Desorption Studies of Reaction Kinetics on Si(111)7x7"

Journal: <u>Proceedings of MicroProcess '89</u> Japan Journal of Applied Physics (1990)

12. Authors: S.M. George, P. Gupta, B.G. Koehler, P.A. Coon, A.C. Dillon and C.H. Mak

Title: "Silicon Surface Kinetics Studied Using Laser Induced Thermal Desorption"

Journal: Laser Photoinization and Desorption Surface Analysis Techniques, SPIE Conference Proceedings, (SPIE, Bellingham, WA., 1990) 13. Authors: S.M. George, P. Gupta, B.G. Koehler, P.A. Coon, A.C. Dillon and C.H. Mak

Title: "Optical Probes of Silicon Surface Chemistry"

Journal: Proceedings of Sixth International Symposium on Silicon Materials Science and Technology, Journal of Electrochemical Society

### VI. Invited Talks on Supported Work

1. "Diffusion and Desorption of Hydrogen on Surfaces"

Xerox Palo Alto Research Center Electronics Materials Laboratory Palo Alto, Calif. June 19, 1987

2. "Diffusion and Desorption of Hydrogen on Surfaces"

Signetics Phillips Research Center Sunnyvale, Calif. June 23, 1987

3. "Oxidation Kinetics of Silicon Surfaces in the Submonolayer Regime"

Intel Corporation Santa Clara, Calif. April 26, 1988

4. "Reaction Kinetics on Si(111) 7x7 Studied Using Laser Induced Thermal Desorption"

Xerox Palo Alto Research Center Electronics Materials Laboratory Palo Alto, Calif. Sept. 9, 1988

5. "Reaction Kinetics on Silicon Surfaces"

Dept. of Chemistry Massachusetts Inst. of Technology Cambridge, Mass. Sept. 13, 1988

6. "Reaction Kinetics on Silicon Surfaces"

Hewlett-Packard Research Center Palo Alto, Calif. Oct. 18, 1988

7. "Oxidation Kinetics of Silicon Surfaces"

Symposium on Chemical Prospectives in Microelectronics Materials Research Society Fall Meeting Boston, Mass. Dec. 1, 1988

8. "Reaction Kinetics on Si(111)7x7 Studied Using Laser Induced Thermal Desorption"

Department of Chemistry California Institute of Technology Pasadena, Calif. January 24, 1989

9. "Reaction Kinetics on Si(111)7x7 Studied Using Laser Induced Thermal Desorption"

Department of Chemistry University of California at San Diego La Jolla, Calif. January 31, 1989

10. "Reaction Kinetics on Si(111)7x7 Studied Using Laser Induced Thermal Desorption"

Department of Chemistry University of Texas at Austin Austin, Texas Feb. 23, 1989

11. "Reaction Kinetics on Si(111)7x7 Studied Using Laser Induced Thermal Desorption"

Department of Chemistry Texas A & M University College Station, Texas Feb. 24, 1989

1°. "Oxidation Kinetics of Silicon Surfaces"

Topical Meeting on Microphysics of Surfaces, Beams and Adsorbates
Salt Lake City, Utah
February 27, 1989

13. "Reaction Kinetics on Si(111)7x7 Studied Using Laser Induced Thermal Desorption"

Dept. of Chemistry Princeton University Princeton, NJ March 15, 1989 14. "Reaction Kinetics on Si(111)7x7 Studied Using Laser Induced Thermal Desorption"

Dept. of Chemistry University of Pennsylvania Philadelphia, Penn. March 16, 1989

15. "Reaction Kinetics on Si(111)7x7 Studied Using Laser Induced Thermal Desorption"

ATT Bell Laboratories Murray Hill, NJ March 17, 1989

16. "Studies of Reaction Kinetics on Silicon Surfaces Using FTIR"

Stanford Materials Research Forum Dept. of Materials Science and Engineering Stanford University Stanford, CA May 5, 1989

17. "Laser Induced Thermal Desorption Studies of Reaction Kinetics on Si(111) 7x7"

International MicroProcess Conference 1989 Japan Society of Applied Physics Kobe, Japan July 4, 1989

18. "Reaction Kinetics on Si(111): 7x7 Surfaces Studied Using Laser-Induced Thermal Desorption"

Condensed Matter Seminar Univ. of California at Berkeley Berkeley, Calif. September 20, 1989

19. "Surface Kinetics Studies Using Laser-Induced Thermal Desorption"

Symposium on Laser Photoionization and Desorption Surface Analysis Techniques SPIE National Meeting Los Angeles, Calif. January 18, 1990 20. "Reaction Kinetics on Si(111)7x7 Studied Using Laser-Induced Thermal Desorption"

Gordon Research Conference on The Chemistry of Electronic Materials Ventura, Calif.
March 1, 1990

### VII. Contributed Talks on Supported Work

1. "Transmission FTIR Studies of Porous Silicon"

P. Gupta, V.L. Colvin and S.M. George

Am. Chem. Soc. Natl. Meeting Denver, Colorado April 10, 1987

2. "Hydrogen Desorption Kinetics from Mono and Dihydride Species on Silicon Surfaces Using Transmission FTIR"

P. Gupta, V.L. Colvin, J.L. Brand and S.M. Ceorge

Am. Vac. Soc. Natl. Meeting Anaheim, Calif. Nov. 3, 1987

"Oxidation Kinetics of Silicon Surfaces in the Submonolayer Regime"

P. Gupta, C.H. Mak, P.A. Coon and S.M. George

ACS Symposium on "General Papers in Catalysis" Natl. Meeting of the American Chemical Society Los Angeles, Calif. Sept. 28, 1988

4. "Oxidation Kinetics of Silicon Surfaces in the Submonolayer Regime"

P. Gupta, C.H. Mak, P.A. Coon and S.M. George

Pacific Conference on Chemistry and Spectroscopy San Francisco, Calif. Oct. 26, 1988

5. "Decomposition of NH<sub>3</sub> on Si(111)7x7 Studied Using Laser Induced Thermal Desorption"

B.G. Koehler, P.A. Coon and S.M. George

Topical Meeting on Microphysics of Surfaces, Beams and Adsorbates
Salt Lake City, Utah
March 1, 1989

6. "Decomposition of NH<sub>3</sub> on Si(111) 7x7 Studied Using Laser-Induced Thermal Desorption"

B.G. Koehler, P.A. Coon, and S.M. George

Northern Calif. Am. Vacuum Society Meeting Stanford Linear Accelerator Center Stanford, Calif. June 1, 1989

7. "Decomposition of NH<sub>3</sub> on Si(111) 7x7 Studied Using Laser-Induced Thermal Desorption"

B.G. Koehler, P.A. Coon, and S.M. George

Sixty-third Colloid and Surface Science Symposium Sponsored by the American Chemical Society University of Washington Seattle, Wash.
June 21, 1989

8. "Adsorption and Desorption of Si Cl<sub> $\Delta$ </sub> on Si(111) 7x7"

P. Gupta, P.A. Coon, B.G. Koehler, and S.M. George

Sixty-third Colloid and Surface Science Symposium Sponsored by the American Chemical Society University of Washington Seattle, Washington June 21, 1989

9. "Decomposition of  $NH_3$  and  $H_20$  on Si(111) 7x7 Studied Using Laser-Induced Thermal Desorption"

B.G. Koehler, P.A. Coon, C.H. Mak and S.M. George

Gordon Research Conference on Inorganic Thin Films and Interfaces
Plymouth Academy
Plymouth, New Hampshire
July 5, 1989

10. "Laser Induced Thermal Desorption for Studies of Surface Reaction Kinetics"

S.M. George, B.G. Koehler, C.H. Mak, P. Gupta and P.A. Coon

5th Interdisciplinary Laser Science Conference Stanford University Stanford, Calif. August 30, 1989 11. "Laser Heating and Laser-Induced Desorption:
Experimental and Theoretical Results for Silicon
Surfaces"

B.G. Koehler, P. Gupta, P.A. Coon and S.M. George

5th Interdisciplinary Laser Science Conference Stanford University Stanford, Calif. August 30, 1989

12. "Decomposition of  $NH_3$  on Si(111) 7x7 Studied Using Laser-Induced Thermal Desorption"

B.G. Koehler, P.A. Coon, P. Gupta and S.M. George

Am. Vac. Soc. Natl. Meeting Boston, Mass. October 24, 1989

13. "Adsorption and Desorption Kinetics for SiCl<sub>4</sub> on Si(111) 7x7"

P. Gupta, P.A. Coon, B.G. Koehler and S.M. George

Am. Vac. Soc. Natl. Meeting Boston, Mass. October 26, 1989

14. "Oxidation Kinetics of Si(111) 7x7 in the Submonolayer Regime"

S.M. George, P. Gupta, C.H. Mak and P.A. Coon

Am. Inst. Chem. Eng. 1989 Annual Meeting Symposium on Kinetics and Mechanisms in Electronics Materials Processing San Francisco, Calif. Nov. 8, 1989

15. "Adsorption and Desorption Kinetics for  $SiCl_4$  on Si(111) 7x7"

P. Gupta, P.A. Coon, B.G. Koehler and S.M. George

Am. Inst. Chem. Eng. 1989 Annual Meeting Symposium on Kinetics and Mechanisms in Electronics Materials Processing San Francisco, Calif. Nov. 9, 1989 16. "Kinetics of  $H_2$ 0 Adsorption and Decompostion on Si(111) 7x7"

B.G. Koehler, P.A. Coon, P. Gupta and S.M. George

Am. Inst. Chem. Eng. 1989 Annual Meeting Symposium on Kinetics and Mechanisms in Electronics Materials Processing San Francisco, Calif. Nov. 9, 1989

### VIII. Contributed Posters on Supported Work

- 1. "Porous Silicon: Chemical and Physical Characterization"
  - P. Gupta and S.M. George

Gordon Research Conf. on the Chemistry of Electronic Materials St. Paul's Academy, Concord, New Hampshire August 20, 1986

- 2. "Transmission FTIR Spectroscopy on Porous Silicon"
  - P. Gupta and S.M. George

Western Spectroscopy Association Annual Conf. Asilomar, Calif. Jan. 29, 1987

- 3. "Studies of Adsorbates on Porous Silicon Using Transmission FTIR Spectroscopy"
  - P. Gupta, J.L. Brand and S.M. George

Northern Calif. Am. Vac. Soc. Meeting IBM Almaden Research Center San Jose, Calif. Feb. 25, 1987

- 4. "Desorption Kinetics of Hydrogen from Silicon Surfaces Using Transmission FTIR"
  - P. Gupta, V.L. Colvin and S.M. George

Gordon Research Conf. on the Dynamics of Gas-Surface Interactions Proctor Academy, Andover, New Hampshire Aug. 13, 1987

- 5. "Desorption Kinetics of Hydrogen From Si(111)7x7 Measured Using Laser-Induced Thermal Desorption"
  - B.G. Koehler, C.H. Mak, D.A. Arthur and S.M. George

Gordon Research Conf. on the Chemistry of Thin Films Colby-Sawyer College New London, New Hampshire Aug. 12, 1987 6. "Hydrogen Desorption Kinetics and Oxygen Reaction Kinetics on Silicon Surfaces"

P. Gupta, V.L. Colvin and S.M. George

Northern Calif. Am. Vac. Soc. Meeting Sandia Natl. Lab. Livermore, Calif. Dec. 9, 1987

7. "Hydrogen Desorption Kinetics from Si(111)7x7 Studied Using Laser-Induced Thermal Desorption"

B.G. Koehler, C.H. Mak, D.A. Arthur, P.A. Coon and S.M. George

Northern Calif. Am. Vac. Soc. Meeting Sandia Natl. Lab. Livermore, Calif. Dec. 9, 1987

8. "Initial Oxygen Reactions Kinetics on Silicon Surfaces"

P. Gupta, V. Colvin and S.M. George

Gordon Research Conf. on Chemistry of Electronic Materials Ventura, Calif.
March 7-11, 1988

9. "Desorption Kinetics of Hydrogen and Deuterium From Si(111) 7x7 Studied Using Laser-Induced Thermal Desorption"

B.G. Koehler, C.H. Mak, D.A. Arthur, P.A. Coon, and S.M. George

Gordon Research Conf. on Chemistry of Electronic Materials Ventura, Calif.
March 7-11, 1988

10. "The Effects of Decomposition Products on the Reaction of Water with Si(111) 7x7"

B.G. Koehler, C.H. Mak, S.M. George

Gordon Research Conf. on Chemistry of Electronic Materials Ventura, Calif.
March 7-11, 1988

11. "Initial Oxygen Reaction Kinetics on Silicon Surfaces"

P. Gupta, V.L. Colvin and S.M. George

Gordon Research Conf. on Chemistry of Electronic Materials Ventura, Calif. March 7-11, 1988

12. "Desorption Kinetics of Hydrogen and Deuterium from Si(111) 7x7 Studied Using Laser-Induced Thermal Desorption"

B.G. Koehler, C.H. Mak, D.A. Arthur, P.A. Coon and S.M. George

Gordon Research Conf. on Chemistry of Electronic Materials Ventura, Calif. March 7-11, 1988

13. "The Effects of Decomposition Products of the Reaction of Water with Si(111) 7x7"

B.G. Koehler, C.H. Mak, S.M. George

Gordon Research Conf. on Chemistry of Electronic Materials Ventura, Calif. March 7-11, 1988

14. "Laser-Induced Thermal Desorption of Silicon-Containing Intermediates from Si(111) 7x7"

C.H. Mak, B.G. Koehler and S.M. George

Gordon Research Conf. on Chemistry of Electronic Materials Ventura, Calif. March 7-11, 1988

15. "Oxidation Kinetics of Silicon Surfaces in the Submonolayer Regime"

P. Gupta, C.H. Mak, P.A. Coon, and S.M. George

Northern Calif. Am. Vacuum Society Meeting IBM Almaden Research Center San Jose, Calif. June 3, 1988 16. "The Decomposition of H20 on Si(111)7x7: Effect of Preadsorbed Hydrogen and Observation of Surface Intermediates"

B.G. Koehler, C.H. Mak, and S.M. George

Northern Calif. Am. Vacuum Society Meeting IBM Almaden Research Center San Jose, Calif. June 3, 1988

17. "Adsorption/Desorption Kinetics of SiCl<sub>4</sub> on Si(111) 7X7"

P. Gupta, P.A. Coon, B.G. Koehler and S.M. George

Symposium on Chemical Prospectives in Microelectronics Materials Research Society Fall Meeting Boston, Mass.
Dec. 1, 1988

18. "Decomposition of  $\rm H_20$  on Si(111) 7x7 Studied Using Laser-Induced Thermal Desorption"

B.G. Koehler, P.A. Coon, C.H. Mak, and S.M. George

Northern Calif. Am. Vacuum Society Meeting Stanford Linear Accelerator Center Stanford, Calif. June 1, 1989

19. "Adsorption and Desorption Kinetics for  $SiCl_4$  on Si(111) 7x7"

P. Gupta, P.A. Coon, B.G. Koehler and S.M. George

Northern Calif. Am. Vacuum Society Meeting Stanford Linear Accelerator Center Stanford, Calif. June 1, 1989

20. "The Decomposition of NH<sub>3</sub> on Si(111) 7x7 Studied Using Laser-Induced Thermal Desorption.

B.G. Koehler, P.A. Coon, and S.M. George

Gordon Research Conference on Inorganic Thin Films and Interfaces
Plymouth Academy
Plymouth, New Hampshire
July 5, 1989

21. "Kinetics of  $H_2$ 0 Adsorption and Decomposition on Si(111) 7x7.

B.G. Koehler, P. Gupta, C.H. Mak, P.A. Coon, and S.M. George

Gordon Research Conference on Inorganic Thin Films and Interfaces
Plymouth Academy
Plymouth, New Hampshire
July 5, 1989

22. "Adsorption and Desorption of  $SiCl_4$  on Si(111) 7x7"

P. Gupta, P.A. Coon, B.G. Koehler, and S.M. George

Gordon Research Conference on Inorganic Thin Films and Interfaces
Plymouth Academy
Plymouth, New Hampshire
July 5, 1989

23. "Oxidation Kinetics of Silicon Surfaces in the Submonolayer Regime"

P. Gupta, C.H. Mak, P.A. Coon and S.M. George

Am. Vac. Soc. Natl. Meeting Boston, Mass. October 26, 1989

24. "FTIR Studies of H<sub>2</sub>O and NH<sub>3</sub> Decomposition on Silicon Surfaces"

A.C. Dillon, P. Gupta, A.S. Bracker, M.B. Robinson and S.M. George

Western Spectroscopy Association 37th Annual Conference Asilomar Conference Center Pacific Grove, Calif. January 24-26, 1990

25. "Silicon Hydride Species on Si(111)7x7 Studies using Laser-Induced Thermal Desorption"

P.A. Coon, P. Gupta, B.G. Koehler, and S.M. George

Gordon Research Conference on The Chemistry of Electronic Materials Ventura, Calif.
March 1, 1990

26. "FTIR Studies of NH<sub>3</sub> Decomposition on Silicon Surfaces"
A.C. Dillon, P. Gupta, A.S. Bracker and S.M. George
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27. "Reactions of Chlorosilanes on Si(111)7x7 Studied Using Laser-Induced Thermal Desorption"

P.Gupta, P.A. Coon, B.G. Koehler, and S.M. George

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28. "FTIR Studies of H<sub>2</sub>O Decomposition on Silidon Surfaces"

P. Gupta, A.C. Dillon, A.S. Bracker, M.B. Robinson and S.M. George

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29. "Experimental and Theoretical Studies of H<sub>2</sub> Laser-Induced Thermal Desorption from Si(111)7x7"

B.G. Koehler, P.A. Coon, P. Gupta and S.M. George

Gordon Research Conference on The Chemistry of Electronic Materials Ventura, Calif.
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